Claims

1. A semiconductor substrate cleaning method comprising a step of removing an adhesive layer provided on a semiconductor substrate by use of a remover composition, wherein

the remover composition contains a solvent but no salt; and

the solvent comprises a C8 to C10 linear-chain, saturated, aliphatic hydrocarbon compound,

wherein the adhesive layer is a film formed from an adhesive composition comprising an adhesive component (S) containing a siloxane adhesive which comprises a polyorganosiloxane component (A) being curable through hydrosilylation.

2. A semiconductor substrate cleaning method according to claim 1, wherein the C8 to C10 linear-chain, saturated, aliphatic hydrocarbon compound is at least one species selected from among n-octane, n-nonane, and n-decane.

3. A semiconductor substrate cleaning method according to claim 1 or 2, wherein the adhesive component (S) further comprises at least one species selected from among an acrylic resin adhesive, an epoxy resin adhesive, a polyamide adhesive, a polystyrene adhesive, a polyimide adhesive, and a phenolic resin adhesive.

4. A semiconductor substrate cleaning method according to any one of claims 1 to 3, wherein the adhesive composition contains a releasing agent component (B).

5. A semiconductor substrate cleaning method according to claim 4, wherein the adhesive composition contains the releasing agent component (B) in an amount of 25 mass% or more, with respect to the adhesive component (S).

6. A processed semiconductor substrate production method comprising:

a first step of producing a laminate having a semiconductor substrate, a support substrate, and an adhesive layer formed from an adhesive composition, wherein the adhesive layer is a film formed from an adhesive composition comprising an adhesive component (S) containing a siloxane adhesive which comprises a polyorganosiloxane component (A) being curable through hydrosilylation;

a second step of processing the semiconductor substrate of the produced laminate;

a third step of separating the semiconductor substrate and the adhesive layer from the support substrate; and

a fourth step of removing the adhesive layer on the semiconductor substrate by use of a remover composition, wherein

the remover composition contains a solvent but no salt; and

the solvent comprises a C8 to C10 linear-chain, saturated, aliphatic hydrocarbon compound.

7. A processed semiconductor substrate production method according to claim 6, wherein the C8 to C10 linear-chain, saturated, aliphatic hydrocarbon compound is at least one species selected from among n-octane, n-nonane, and n-decane.

8. A processed semiconductor substrate production method according to claim 6 or 7, wherein the adhesive component (S) further comprises at least one species selected from among an acrylic resin adhesive, an epoxy resin adhesive, a polyamide adhesive, a polystyrene adhesive, a polyimide adhesive, and a phenolic resin adhesive.

9. A processed semiconductor substrate production method according to claim 8, wherein the adhesive composition contains a releasing agent component (B).

10. A processed semiconductor substrate production method according to claim 9, wherein the adhesive composition contains the releasing agent component (B) in an amount of 25 mass% or more, with respect to the adhesive component (S).